





TSSOP-8

Pin Definition:

8 1. Drain 1 8. Drain 2 2. Source 1 7. Source 2 3. Source 1 6. Source 2 4. Gate 1 5. Gate 2

PRODUCT SUMMARY

V _{DS} (V)	$R_{DS(on)}(m\Omega)$	I _D (A)
20	22 @ V _{GS} = 4.5V	6.5
	29 @ V _{GS} = 2.5V	5.5

Features

- Advance Trench Process Technology
- High Density Cell Design for Ultra Low On-resistance
- ESD Protect 2KV

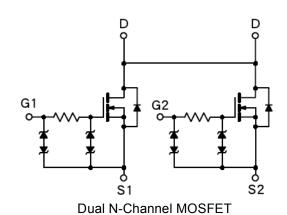
Application

- Specially Designed for Li-on Battery Packs
- Battery Switch Application

Ordering Information

Part No.	Package	Packing
TSM6968DCA RV	TSSOP-8	3Kpcs / 13" Reel

Block Diagram



Absolute Maximum Rating (Ta = 25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage	n-Source Voltage		20	V	
Gate-Source Voltage		V_{GS}	±12	V	
Continuous Drain Current, V _{GS} @4.5\	<i>1</i> .	I _D	6.5	Α	
Pulsed Drain Current, V _{GS} @4.5V		I _{DM}	30	Α	
Continuous Source Current (Diode Co	onduction) ^{a,b}	I _S	1.4	Α	
Maximum Power Dissipation	Ta = 25°C	- P _D	1.5	W	
	Ta = 75°C		0.96		
Operating Junction Temperature		TJ	+150	°C	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C	

Thermal Performance

Parameter	Symbol	Limit	Unit
Junction to Foot (Drain) Thermal Resistance	$R\Theta_{JF}$	30	°C/W
Junction to Ambient Thermal Resistance (PCB mounted)	R⊖ _{JA}	50	°C/W

Notes:

- a. Pulse width limited by the Maximum junction temperature
- b. Surface Mounted on FR4 Board, $t \le 5$ sec.





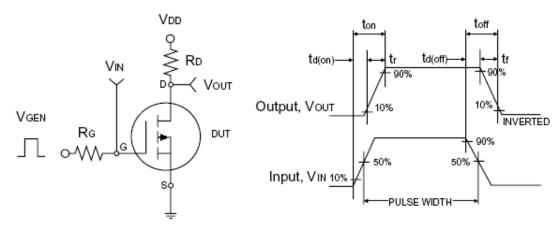
20V Dual N-Channel MOSFET w/ESD Protected

Electrical Specifications (Ta = 25°C, unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250uA$	BV _{DSS}	20			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250uA$	$V_{GS(TH)}$	0.6	8.0	1.0	V
Gate Body Leakage	$V_{GS} = \pm 12V, V_{DS} = 0V$	I _{GSS}			±10	uA
Zero Gate Voltage Drain Current	$V_{DS} = 16V, V_{GS} = 0V$	I _{DSS}			1.0	uA
On-State Drain Current	$V_{DS} = 5V, V_{GS} = 4.5V$	I _{D(ON)}	30			Α
Drain-Source On-State Resistance	On-State Resistance $V_{GS} = 4.5V$, $I_D = 6.0A$		29	32	0	
Drain-Source On-State Resistance	$V_{GS} = 2.5V, I_D = 5.0A$	R _{DS(ON)}		34	40	mΩ
Forward Transconductance	$V_{DS} = 10V, I_D = 6.5A$	g _{fs}		16		S
Diode Forward Voltage	$I_S = 1.7A$, $V_{GS} = 0V$	V_{SD}		0.6	1.2	V
Dynamic ^b						
Total Gate Charge	$V_{DS} = 10V, I_D = 6A,$	Q_g		15	20	
Gate-Source Charge	$V_{DS} = 10V, I_D = 6A,$ $V_{GS} = 4.5V$	Q_{gs}		3.4		nC
Gate-Drain Charge	V _{GS} = 4.5 V	Q_{gd}		1.2		
Input Capacitance	\	C _{iss}		950		
Output Capacitance	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	C _{oss}		450		pF
Reverse Transfer Capacitance	1 - 1.01VII 12	C _{rss}		135		
Switching ^c						
Turn-On Delay Time	V -40V D -400	t _{d(on)}		140	200	
Turn-On Rise Time	$V_{DD} = 10V, R_L = 10\Omega,$ $I_D = 1A, V_{GEN} = 4.5V,$	t _r		210	250	nS
Turn-Off Delay Time	$R_{G} = 6\Omega$	$t_{d(off)}$		3700	4800	113
Turn-Off Fall Time	17G - 022	t_f		2000	2600	

Notes:

- a. pulse test: PW ≤300µS, duty cycle ≤2%
- b. For DESIGN AID ONLY, not subject to production testing.
- b. Switching time is essentially independent of operating temperature.



Switching Test Circuit

Switchin Waveforms

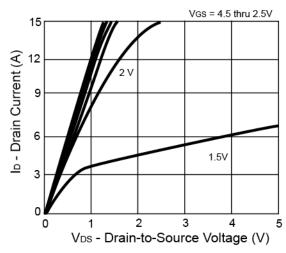




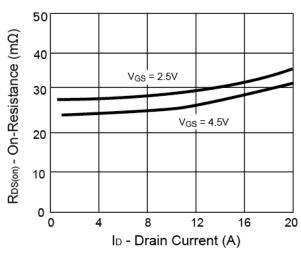


Electrical Characteristics Curve (Ta = 25°C, unless otherwise noted)

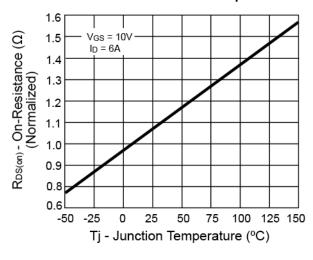




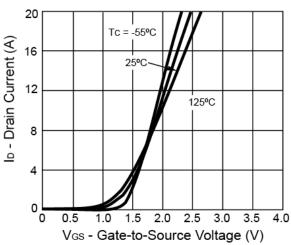
On-Resistance vs. Drain Current



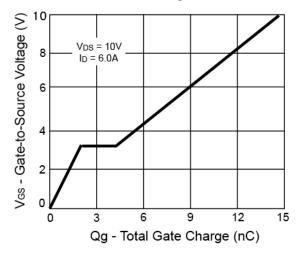
On-Resistance vs. Junction Temperature



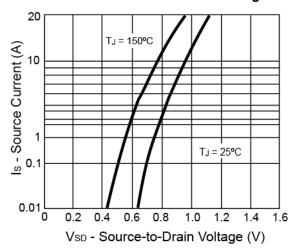
Transfer Characteristics



Gate Charge



Source-Drain Diode Forward Voltage



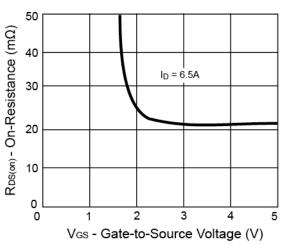




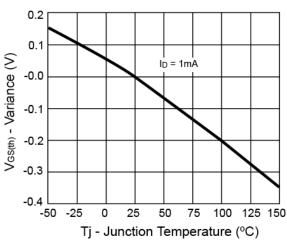


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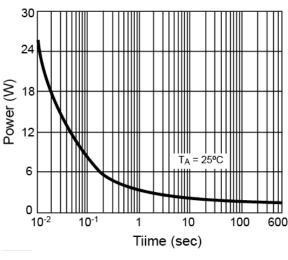




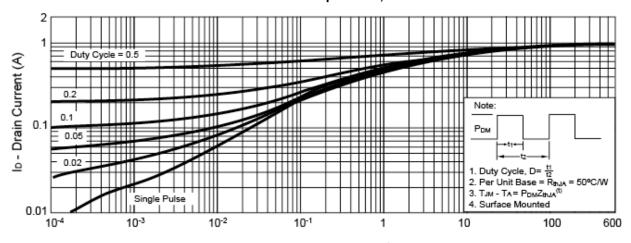
Threshold Voltage



Single Pulse Power



Normalized Thermal Transient Impedance, Junction-to-Ambient



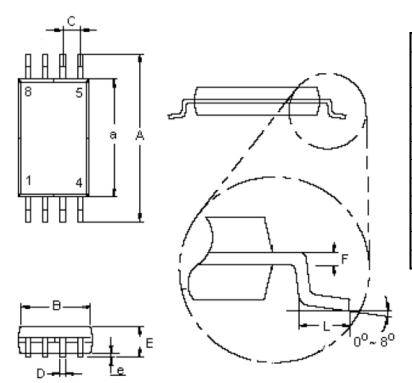
Square Wave Pulse Duration (sec)





20V Dual N-Channel MOSFET w/ESD Protected

TSSOP-8 Mechanical Drawing



TSSOP-8 DIMENSION					
DIM	MILLIMETERS		INCHES		
	MIN	MAX	MIN	MAX	
Α	6.20	6.60	0.244	0.260	
а	4.30	4.50	0.170	0.177	
В	2.90	3.10	0.114	0.122	
C	0.65 (typ)		0.025 (typ)		
D	0.25	0.30	0.010	0.019	
Е	1.05	1.20	0.041	0.049	
е	0.05	0.15	0.002	0.009	
e F	0.05 0.127	0.15		0.009 005	
		0.15			

Marking Diagram



Y = Year Code

M = Month Code

(A=Jan, B=Feb, C=Mar, D=Apl, E=May, F=Jun, G=Jul, H=Aug, I=Sep, J=Oct, K=Nov, L=Dec)

L = Lot Code



20V Dual N-Channel MOSFET w/ESD Protected

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